

## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

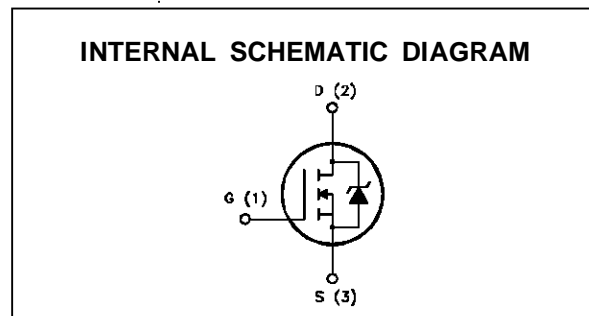
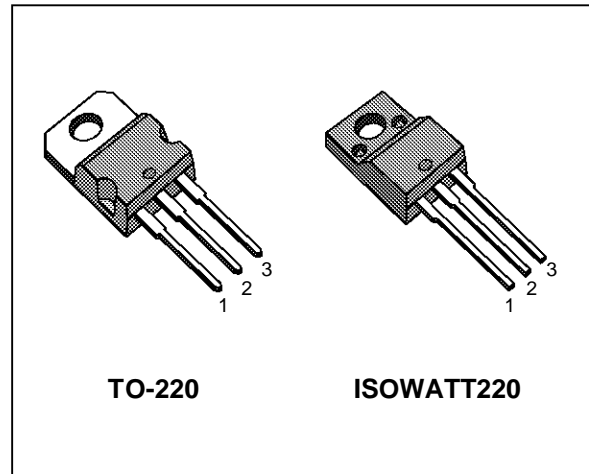
PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
IRF630	200 V	< 0.4 Ω	10 A
IRF630FI	200 V	< 0.4 Ω	6 A

- TYPICAL R<sub>DS(on)</sub> = 0.25 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION

### APPLICATIONS

- HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- MOTOR CONTROL, AUDIO AMPLIFIERS
- INDUSTRIAL ACTUATORS
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT
- PARTICULARLY SUITABLE FOR ELECTRONIC FLUORESCENT LAMP BALLASTS



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		IRF630	IRF630FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	200		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	200		V
V <sub>GS</sub>	Gate-source Voltage	± 20		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	10	6	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	6	3	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	40	40	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	100	35	W
	Derating Factor	0.8	0.28	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	2000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

**THERMAL DATA**

			TO-220	ISOWATT220	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.25	3.57	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

**AVALANCHE CHARACTERISTICS**

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	10	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	60	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	15	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	6	A

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	200			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C			250 1000	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

**ON (\*)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 5 A V <sub>GS</sub> = 10V I <sub>D</sub> = 5 A T <sub>c</sub> = 100°C		0.25	0.4 0.8	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	10			A

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)max</sub> I <sub>D</sub> = 5 A	3	7		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1100	1500	pF
C <sub>oss</sub>	Output Capacitance			160	250	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			30	50	pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 100\text{ V}$ $I_D = 5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		40 80	60 120	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 200\text{ V}$ $I_D = 10\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		250		A/ $\mu$ s
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 200\text{ V}$ $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$		40 8 10	60	nC nC nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 200\text{ V}$ $I_D = 10\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		50 30 80	80 50 130	ns ns ns

**SOURCE DRAIN DIODE**

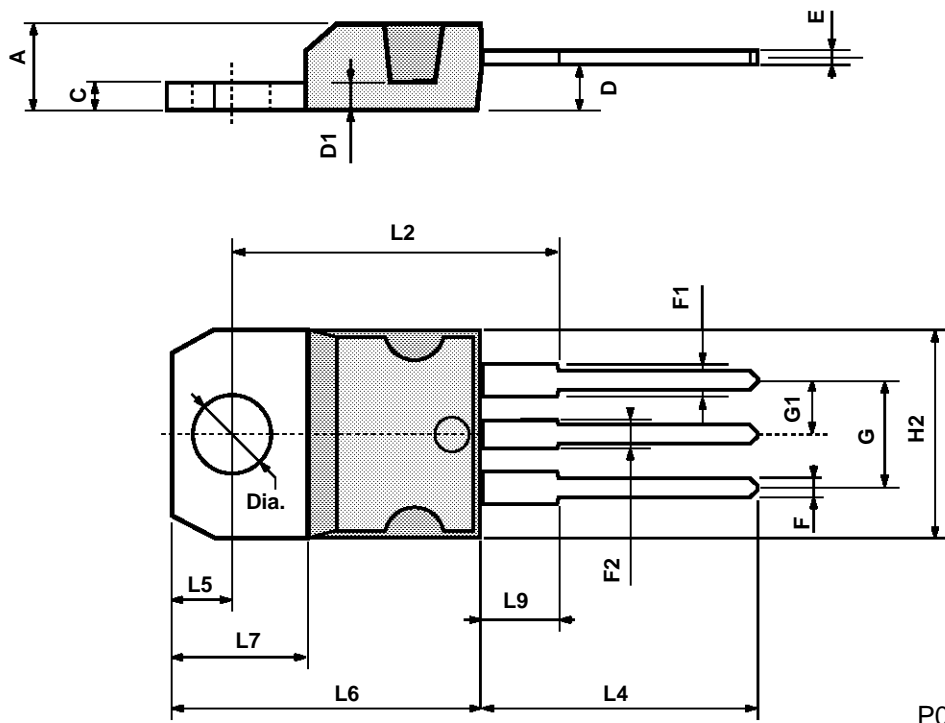
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				10 40	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 10\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 10\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		300 3 20		ns $\mu$ C A

(\*) Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

**TO-220 MECHANICAL DATA**

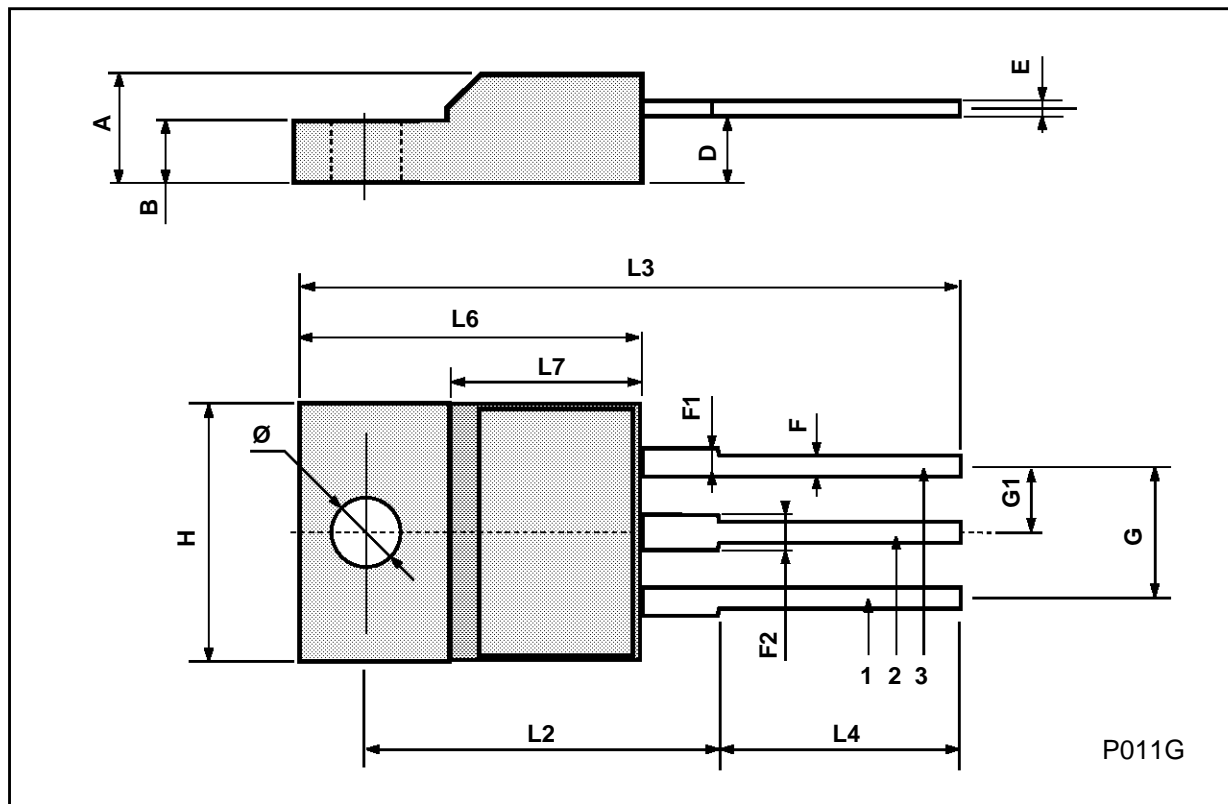
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

## ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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